

Switching diode

1SS133

●Applications

High speed switching

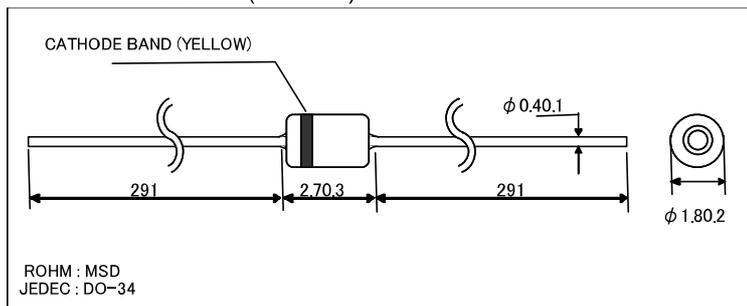
●Features

- 1) Glass sealed envelope. (MSD)
- 2) High reliability.

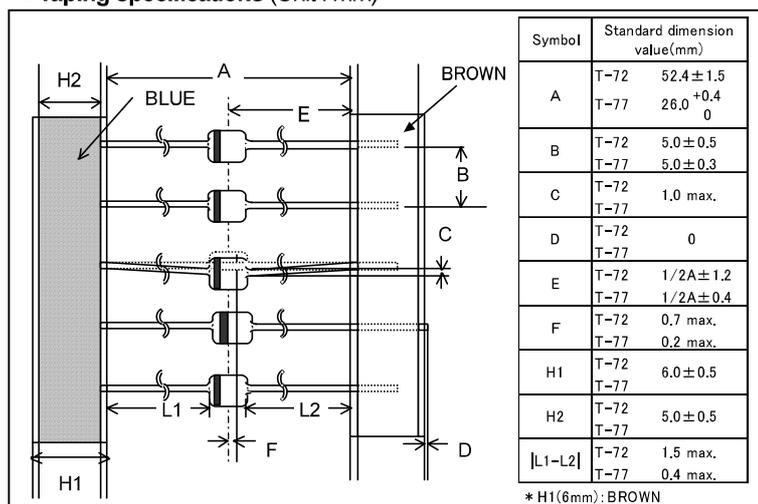
●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



●Taping specifications (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	90	V
Reverse voltage (DC)	V_R	80	V
Forward voltage (repetitive peak)	I_{FM}	400	mA
Average rectified forward current	I_o	130	mA
Surge current (1s)	I_{surge}	600	mA
Power dissipation	P	300	mW
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to 175	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	$I_F=100mA$
Reverse current	I_R	-	-	0.5	μA	$V_R=80V$
Capacitance between terminal	C_t	-	-	2	pF	$V_R=0.5V, f=1MHz$
Reverse recovery time	T_{rr}	-	-	4.0	ns	$V_R=6V, I_F=10mA, R_L=50\Omega, I_{rr}=1/10 I_R$